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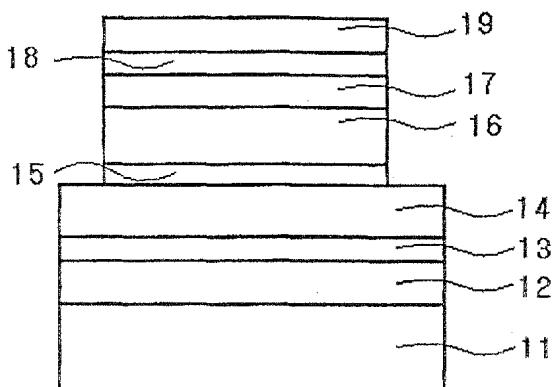
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(54) Title: GALLIUM NITRIDE-BASED III-V GROUP COMPOUND SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME



(57) Abstract: The present invention relates to a gallium nitride-based compound semiconductor device and a method of manufacturing the same. According to the present invention, there is provided a gallium nitride-based II-V group compound semiconductor device comprising a gallium nitride-based semiconductor layer and an ohmic electrode layer formed on the gallium nitride-based semiconductor layer. The ohmic electrode layer comprises a contact metal layer, a reflective metal layer, and a diffusion barrier layer.